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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **KANO, Takashi**

Group Art Unit: 2828

Serial No.: 09/532,775

Examiner: Tuan M. Nguyen

Filed: March 22, 2000

P.T.O. Confirmation No.: 8757

For: **SEMICONDUCTOR LASER DEVICE**

SUPPLEMENTAL AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
Washington, D.C. 20231
Sir:

April 23, 2003

In response to the Office Action dated April 10, 2003, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1-3 as indicated below:

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TECHNOLOGY CENTER 2800

1. (Amended) A semiconductor laser device comprising:

a first nitride based semiconductor layer including a first conductivity type cladding layer and an active layer and containing at least one of boron, aluminum, gallium, indium and thallium;

a current blocking layer, formed on said first nitride based semiconductor layer, having a striped opening; and

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